

isc Silicon PNP Power Transistor

ISCB730P

DESCRIPTION

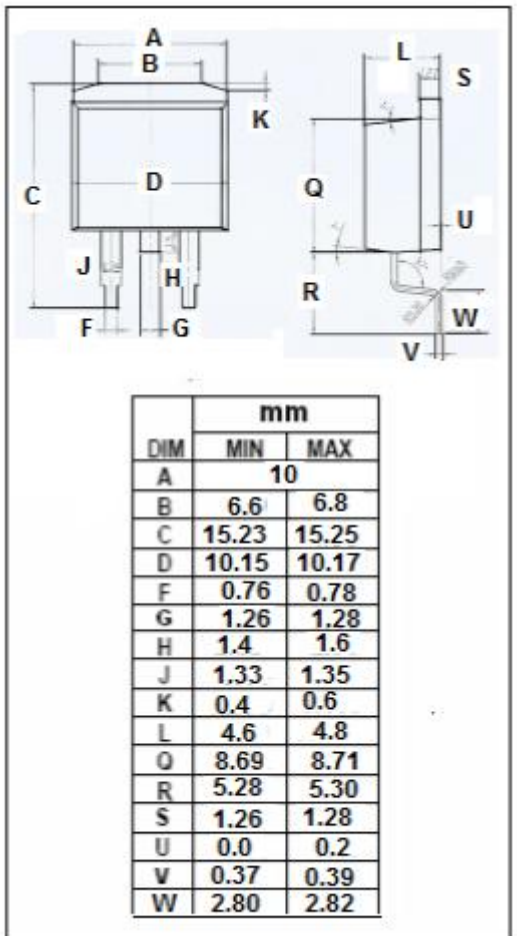
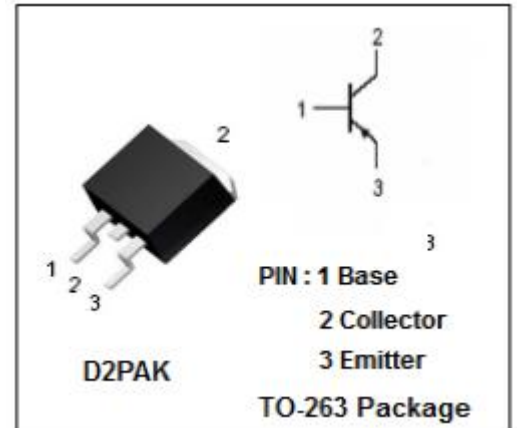
- With TO-263 packaging
- Good Linearity of h_{FE}
- High Collector-Emitter Breakdown Voltage-
 $V_{(BR)CEO} = -250V$ (Min)
- Wide Area of Safe Operation
- Complement to Type ISCB730N

APPLICATIONS

- Audio frequency power amplifier
- High frequency power amplifier

ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-250	V
V_{CEO}	Collector-Emitter Voltage	-250	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_C	Collector Current-Continuous	-1.5	A
I_{CM}	Collector Current-Peak	-3.0	A
P_C	Collector Power Dissipation@ Tc=25°C	10	W
T_J	Junction Temperature	150	°C
T_{stg}	Storage Temperature Range	-55~150	°C



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ELECTRICAL CHARACTERISTICS

T_c=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C = -500mA; I _B = -50mA			-1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -150V; I _E = 0			-1.0	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3.0V; I _C =0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -5mA ; V _{CE} = -5V	30			
h _{FE-2}	DC Current Gain	I _C = -150mA ; V _{CE} = -5V	60		320	
f _T	Current-Gain—Bandwidth Product	I _C = -100mA ; V _{CE} = -10V		80		MHz
C _{OB}	Output Capacitance	I _E = 0 ; V _{CB} = -10V;f= 1.0MHz		45		pF

◆ **h_{FE-2} Classifications**

R	Q	P
60-120	100-200	160-320